Shantou Huashan Electronic Devices Co.,Ltd.

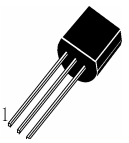
PNP SILICON TRANSISTOR

H643

APPLICATIONS

Low frequency power amplifier

TO-92



1—Emitter，E
2—Base，B
3—Collector，C

ABSOLUTE MAXIMUM RATINGS（T_a=25℃）

T_{stg}——Storage Temperature…… -55~150℃

T_j——Junction Temperature……150℃

P_C——Collector Dissipation……500mW

V_{CBO}——Collector-Base Voltage……-40V

V_{CEO}——Collector-Emitter Voltage……-20V

V_{EBO}——Emitter-Base Voltage……-5V

I_C——Collector Current……-500mA

ELECTRICAL CHARACTERISTICS（T_a=25℃）

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	-40			V	I_C=-100μA, I_E=0
BV_{CEO}	Collector-Emitter Breakdown Voltage	-20			V	I_C=-10mA, I_B=0
BV_{EBO}	Emitter-Base Breakdown Voltage	-5			V	I_E=-10μA，I_C=0
I_{CBO}	Collector Cut-off Current			-200	nA	V_{CB}=-25V, I_E=0
I_{EBO}	Emitter Cut-off Current			-200	nA	V_{EB}=-3V, I_C=0
H_{FE}	DC Current Gain	40		400		V_{CE}=-1V, I_C=-100mA
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage		-0.3	-0.4	V	I_C=-500mA, I_B=-50mA
$V_{BE(sat)}$	Base-Emitter Saturation Voltage		-1.0	-1.3	V	I_C=-500mA, I_B=-50mA

h_{FE} Classification

R	O	Y	G
40—80	70—140	120—240	200—400

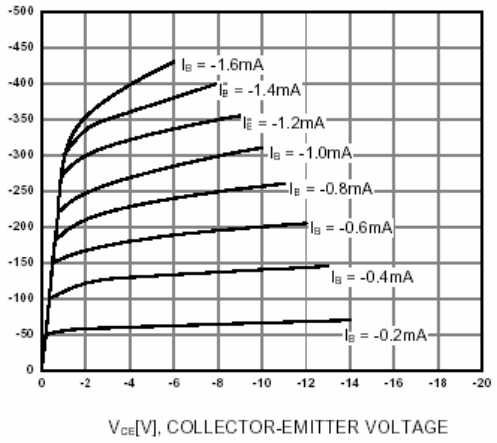


Figure 1. Static Characteristic

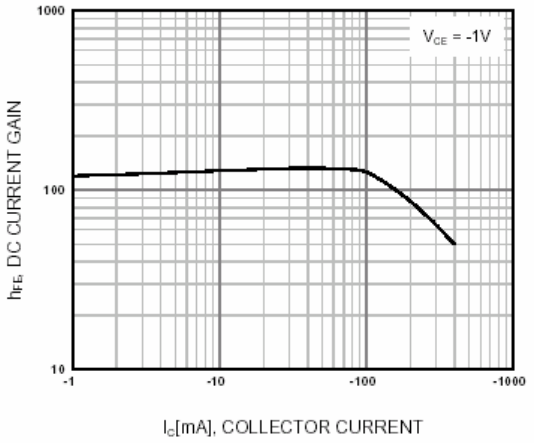


Figure 2. DC current Gain

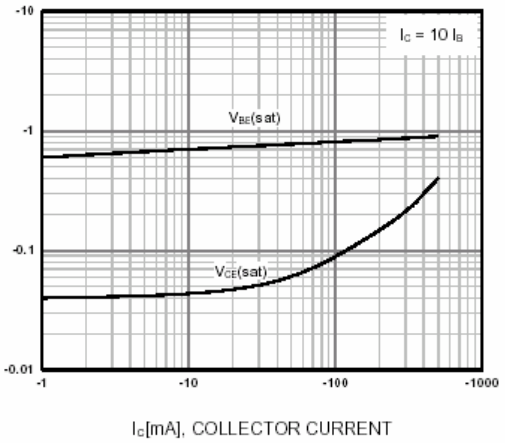


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

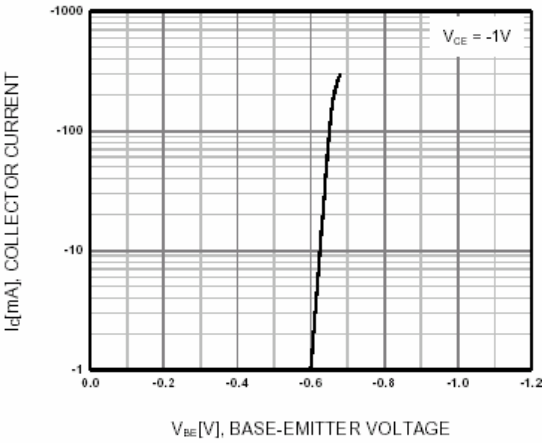


Figure 4. Base-Emitter On Voltage

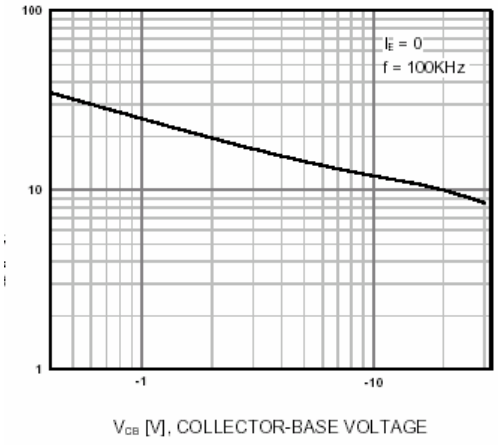


Figure 5. Collector Output Capacitance